

FIG. 1A
(prior art)

00977-84551650

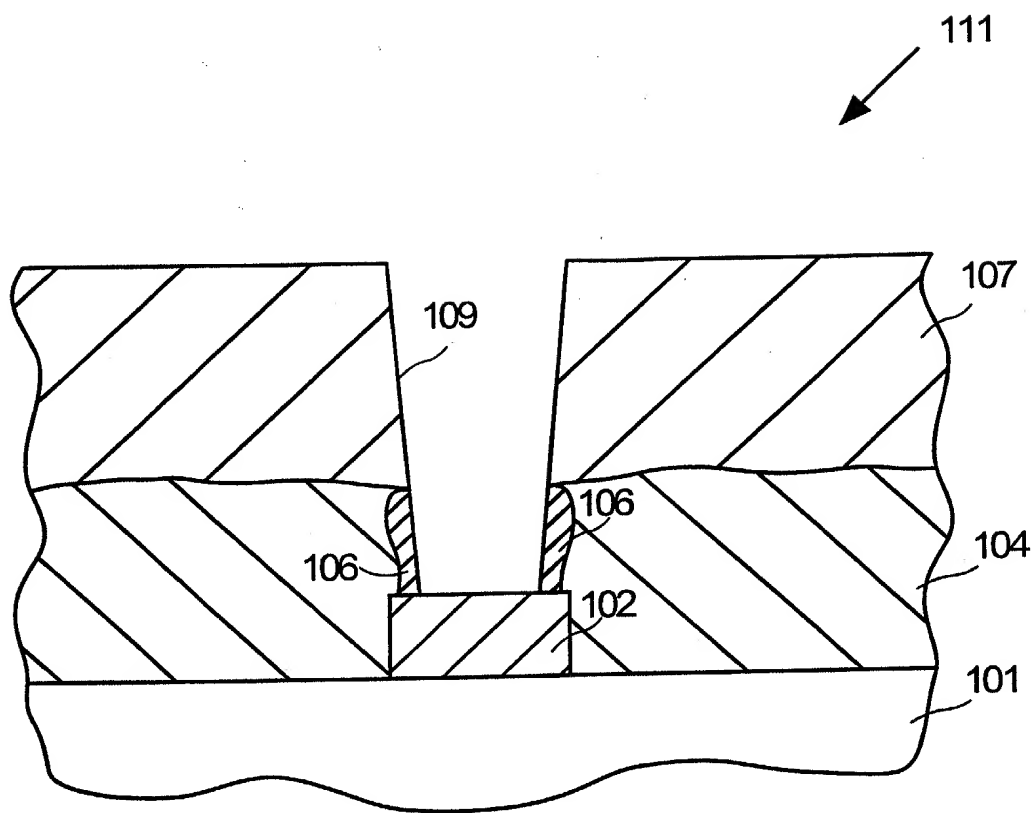


FIG. 1B

009775 62691460

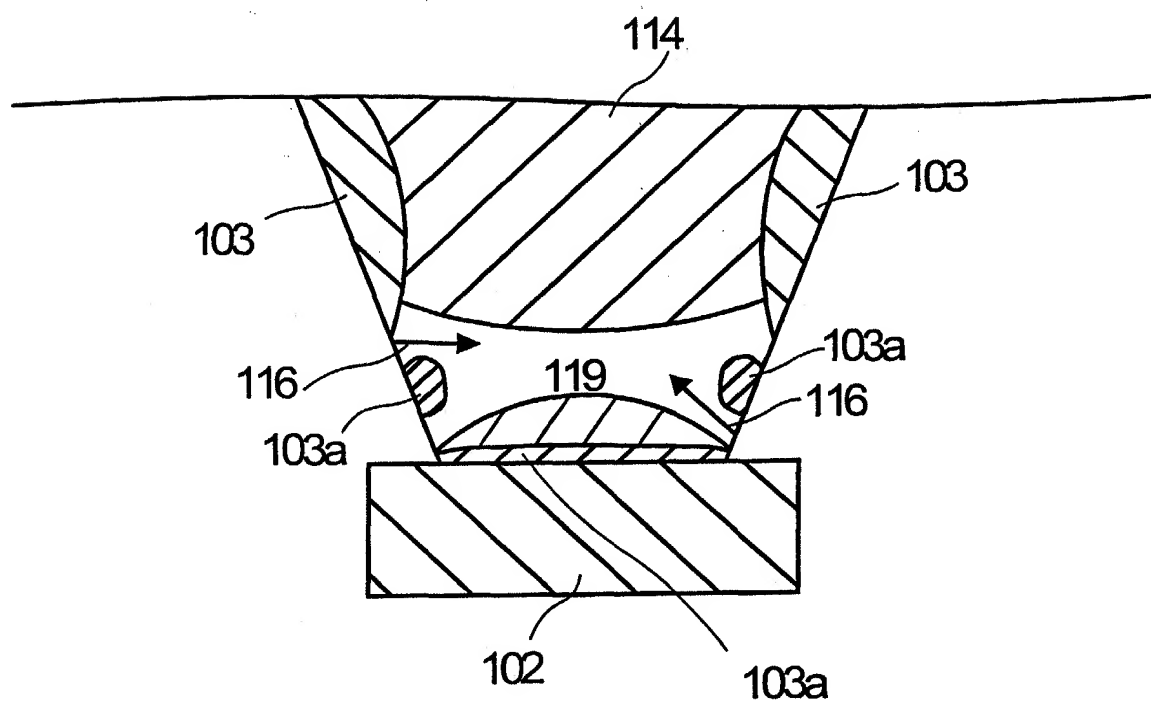


FIG. 1D

09745973-114500

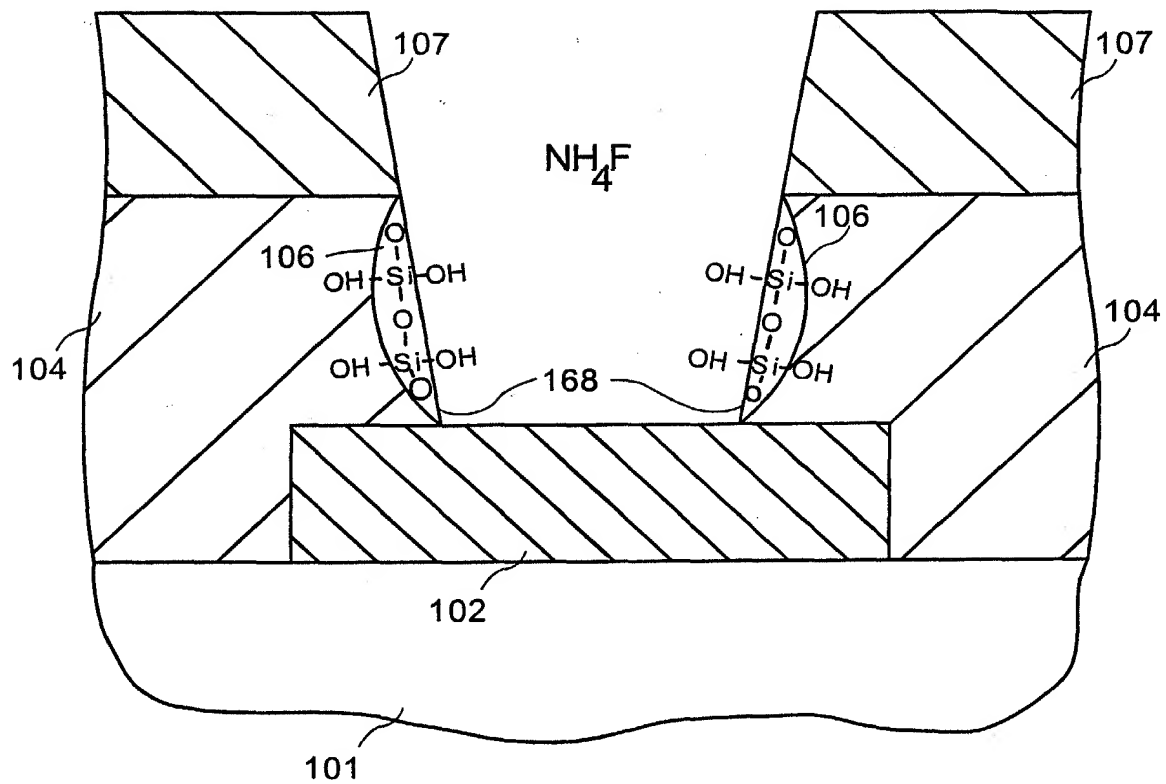


FIG. 2A

00977 24657260

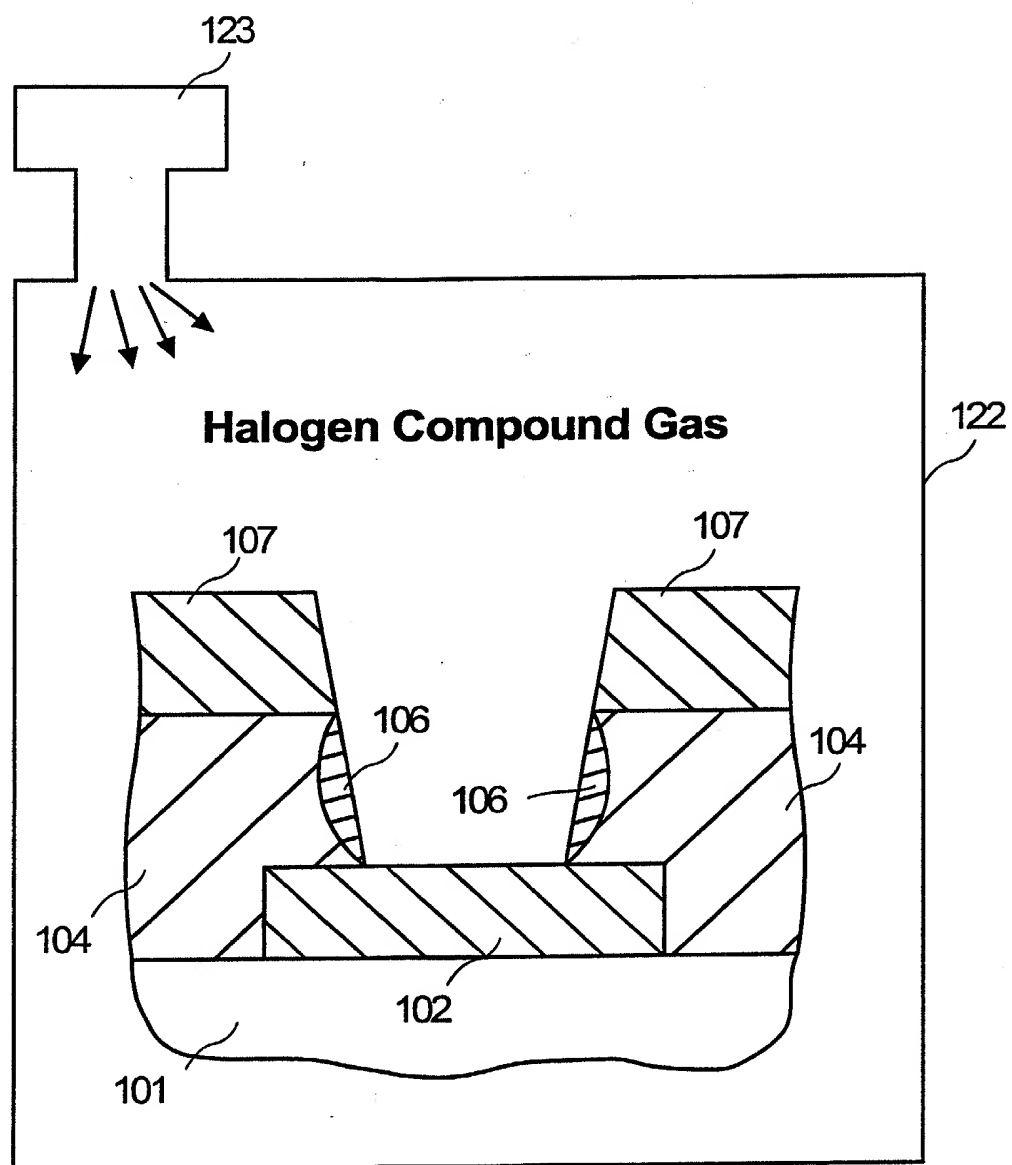


FIG. 2B

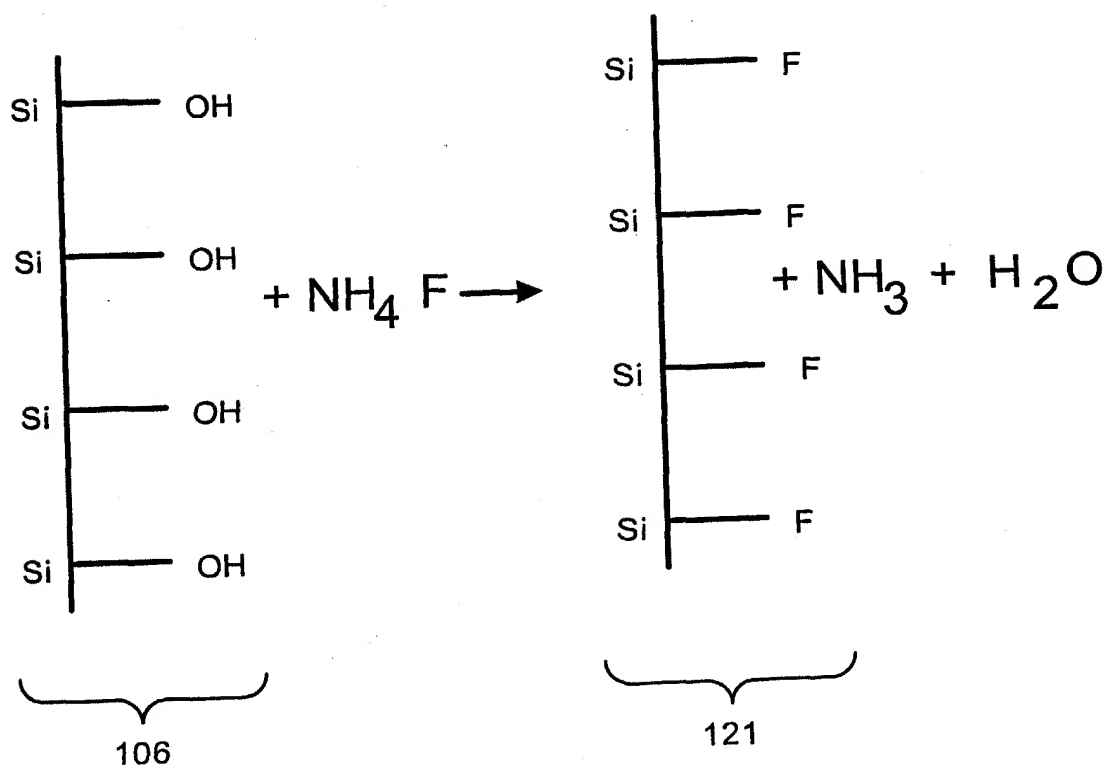
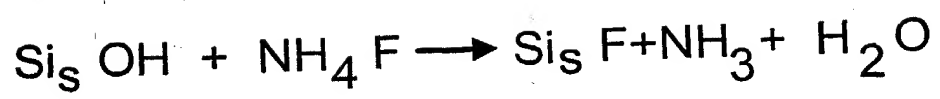
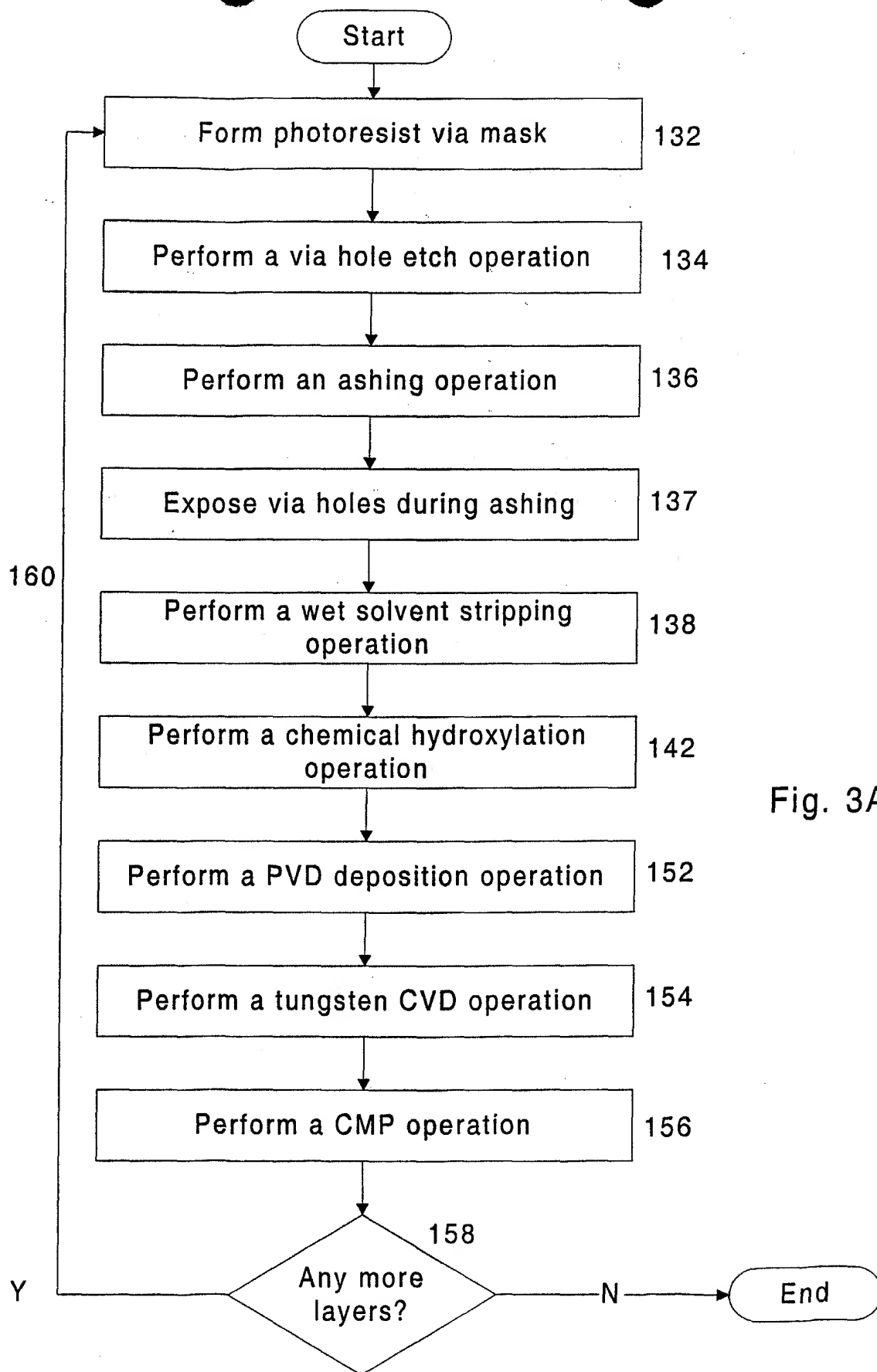


FIG. 2C

A cross-sectional view of a semiconductor device. A substrate 101 is at the bottom. A layer 102 is on top of the substrate. A trench 103 is formed in layer 102. The trench 103 has a bottom surface 104 and side walls 107. A layer 114 is on the top surface of the device. A raised portion 103 is formed on the top surface of the device. The raised portion 103 has a top surface 103 and side walls 107. The side walls 107 of the raised portion 103 are labeled with chemical groups: Si-F, Si-F, and Si-F on the left side, and F-Si, F-Si, and F-Si on the right side. A layer 121 is on the bottom surface 104 of the trench 103.

FIG. 2D



00977 2457400

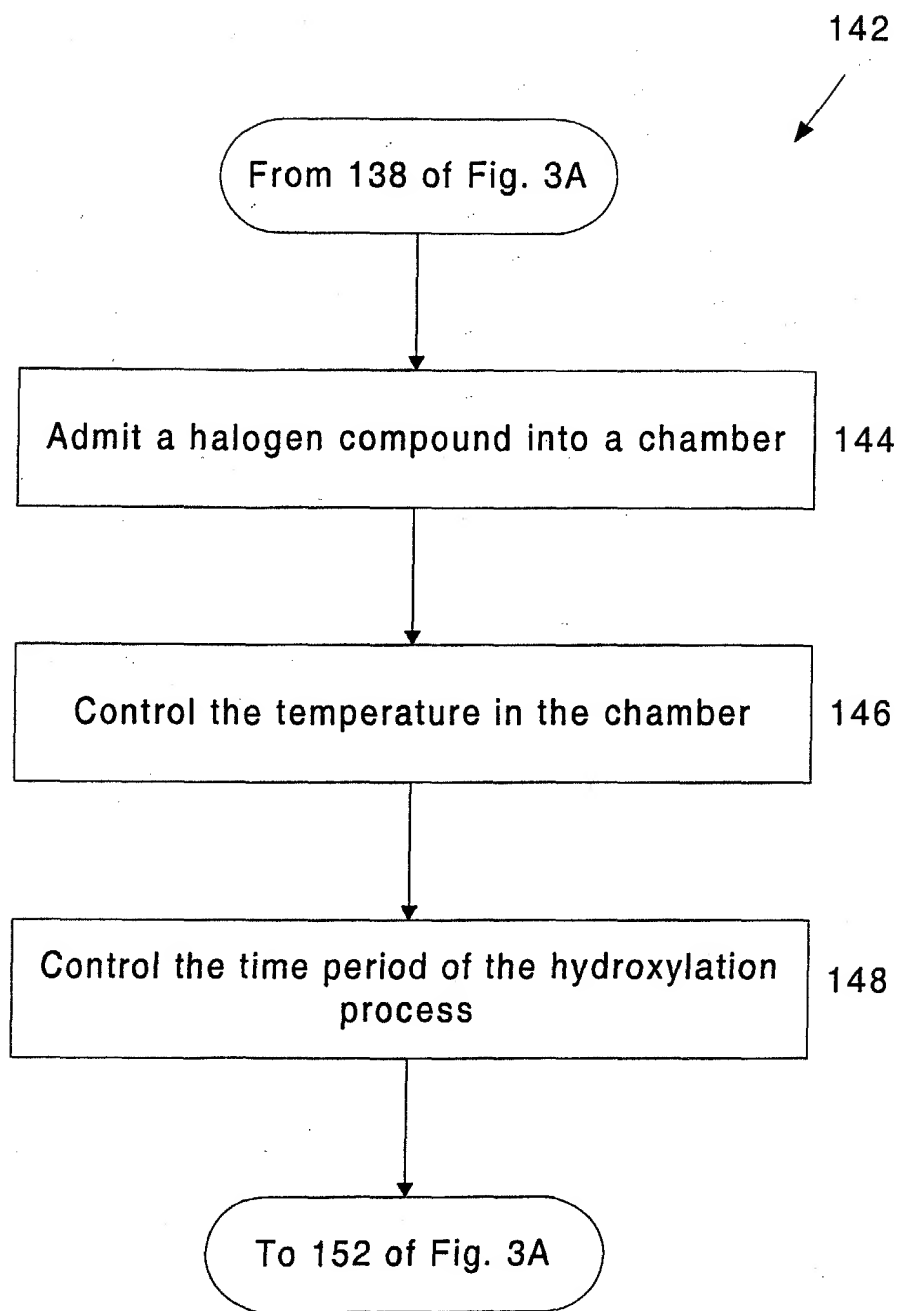


Fig. 3B